

Amendments to the Specification:

Please amend the title of the application as follows:

SET OF AT LEAST TWO MASKS FOR THE PROJECTION OF STRUCTURE

~~PATTERNS AND METHOD OF PRODUCING THE MASKS~~

Please replace the current Abstract with the following new abstract (a replacement sheet of this new abstract is also attached):

A set of at least two masks, coordinated with one another, for the projection of structure patterns, into the same photosensitive layer arranged on a semiconductor wafer. The first mask includes a semitransparent or nontransparent first layer, which is arranged on a first substrate and in which at least one first opening is formed at a first position, the first opening having a first lateral dimension, which is greater than the resolution limit of a projection system for the projection of the structure patterns. The second mask includes a semitransparent or nontransparent second layer, which is arranged on a second substrate and in which at least one dummy structure assigned to the first opening is formed at a second position, the dummy structure having a second lateral dimension, which is smaller than the resolution limit of the projection system wherein the first position on the first mask corresponds to the second position on the second mask.

Please amend the paragraph beginning at page 6, line 13 as follows:

In this case, “identical” means that the positions are identical relative to a system of coordinates of the mask which can be transferred from the first mask to the second mask. This is the case, for example, if the masks have essentially identical external dimensions and their

positional positioning in a mask mount during a projection is defined by markings in the substrate. Consequently, the imaging of the opening and of the dummy structure assigned thereto also fall into the same segment on the image plane, i.e., the photosensitive layer.

Please amend the paragraph beginning at page 14, line 1 as follows:

FIG. 3 shows, in an extension of FIG. 2, dummy gaps 191 to 193 on the primary phase mask. With regard to the dummy structures or gaps 191 to 193, the “second” mask according to the invention is represented by the alternating phase mask P and, with regard to the dummy structures or gaps 291 to 294, the “second” mask according to the invention is represented by the trimming mask T. The dummy gaps 191-193 can produce an additional irradiation of the photosensitive layer R in the exposed segment of the images of the gaps 24 to 26 of the trimming mask. The dummy gaps 191 to 193 can be introduced eccentrically centered with respect to the corresponding gaps 24 to 26 on the trimming mask and have smaller lateral dimensions than the gaps on the trimming mask. Their size can be determined according to the method described above for the trimming mask. The additional exposure with the trimming gaps can increase the depth of focus of the resist structures 36' and 37' produced by double exposure. For the reason already explained above for phase masks, dummy gaps on the phase mask can be used when the Bossung curves of the corresponding webs, in the case of an exclusive (single) exposure with the trimming mask, have a pronounced concave shape and thus lead to a small depth of focus.